ABSTRACT

The polishing pad of this invention is a polishing pad effecting stable planarizing processing, at high polishing rate, materials requiring surface flatness at high level, such as a silicon wafer for semiconductor devices, a magnetic disk, an optical lens etc. This invention provides a polishing pad which can be subjected to surface processing to form a sheet or grooves, is excellent in thickness accuracy, attains a high polishing rate, achieves a uniform polishing rate, and also provides a polishing pad which is free of quality variations resulting from an individual variation, easily enables a change the surface patterns, enables fine surface pattern, is compatible with various materials to be polished, is free of burrs upon forming the pattern. This invention provides a polishing pad which can have abrasive grains mixed at very high density without using slurry, and generates few scratches by preventing aggregation of abrasive grains dispersed therein. The polishing pad of this invention has a polishing layer formed from a curing composition to be cured with energy rays, the polishing layer being formed surface pattern thereon by photolithography. The polishing pad of this invention comprises a polishing layer resin having abrasive grains dispersed therein, the resin containing ionic groups in the range of 20 to 1500 eq/ton.